

5 é / Descriptions

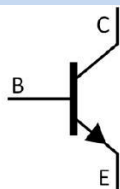
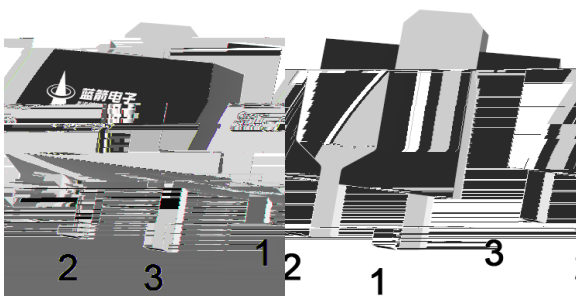
9 5 : .> // x 4 6 4 ! - } â 'ož Silicon NPN transistor in a SOT-89 Plastic Package.

α a / Features

: ; m k —)í D }ož
Complementary pair with 8550T, HF Product.

9 ä y Ý èož
Power amplifier applications.

Ã W] Ô . / Equivalent Circuit



PIN1 y Base PIN 2 y Collector PIN 3 y Emitter

, M V / Marking

h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	85 160	120 200	160 300
Marking	HY1B	HY1C	HY1D

@ f Parameter	... Z Symbol	$f >$ Rating	% y Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Base - Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		

Ô ? d • Ž ¢ / Electrical Characteristic Curve



Ø □ =) ¢ / Package Dimensions

, M y f / Marking Instructions

HY1B

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Note:

H: Company Code

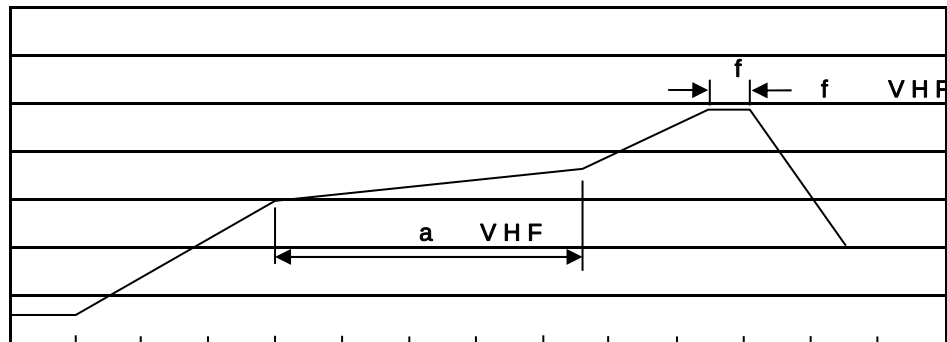
Y1: Product Type

B y h_{FE} Classifications Symbol

** : Lot No. Code, code change with Lot No

šWD t... • Žč (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

7HP SHUDWXXUH



7LPH VHF

a č y

10• Ä ½ “† 150 ½180 - k ž • 60 ½90sec;

20• Q > “† 245 r5 - k ž • 4 Ò 5 r0.5sec;

30•D N ò i Ò 0 ,† 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“† y 260 r5 -

ž • y 10 r1 sec.

Temp.:260±5

Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ~ E	Units ;>û !H					Dimension ;>û p . (unit /mm³)		
	Units/Reel /-	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box	Outer Boxç
SOT-89	1,000	7	7,000	6	42,000	7 s ×12	180×120×180	390×385×205

„Đ y f / Notices